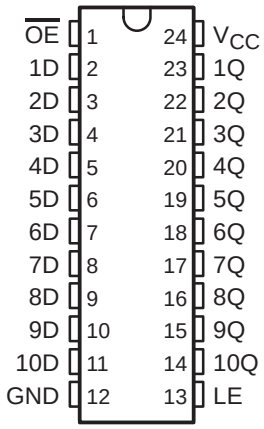
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})**
- **Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages**

DB, DW, OR PW PACKAGE
(TOP VIEW)



description

This 10-bit bus-interface D-type latch is designed for 2.7-V to 3.6-V V_{CC} operation; it can interface to a 5-V system environment.

The SN74LVC841 is designed specifically for driving highly capacitive or relatively low-impedance loads. It is particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers.

The ten latches are transparent D-type latches. The device has noninverting data (D) inputs and provides true data at its outputs.

A buffered output-enable ($\overline{OE}$) input can be used to place the ten outputs in either a normal logic state (high or low levels) or a high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components.

The output-enable ($\overline{OE}$) input does not affect the internal operations of the latch. Previously stored data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74LVC841 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

INPUTS			OUTPUT
$\overline{OE}$	LE	D	Q
L	H	H	H
L	H	L	L
L	L	X	Q_0
H	X	X	Z

PRODUCT PREVIEW

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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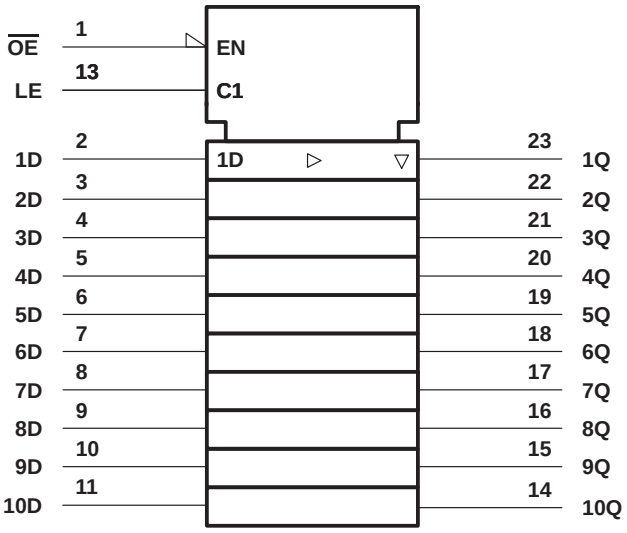
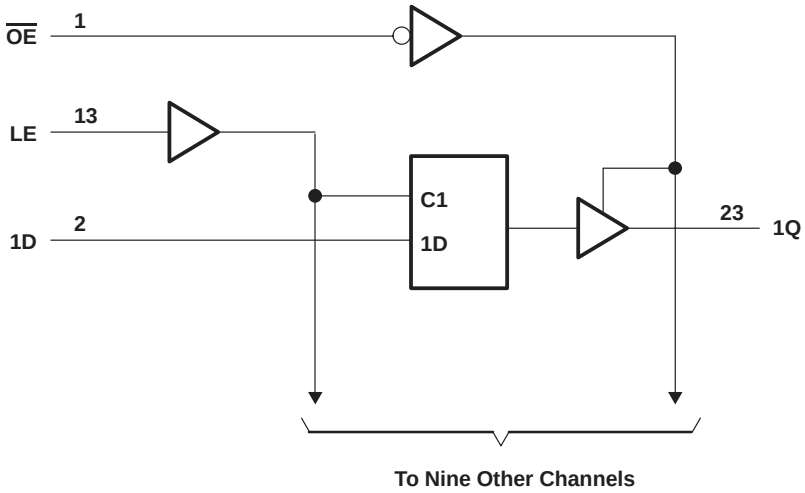
logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 6.5 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high impedance state
or power off state, V_O (see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high
or low state, V_O (see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . – 50 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through V_{CC} or GND . . . . . ±100 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 3): DB package . . . . . 0.65 W
DW package . . . . . 1.7 W
PW package . . . . . 0.7 W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils. For more information, refer to the *Package Thermal Considerations* application note in the 1994 *ABT Advanced BiCMOS Technology Data Book*, literature number SCBD002B.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	2	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 2.7 V to 3.6 V	2		V
V_{IL}	Low-level input voltage	V_{CC} = 2.7 V to 3.6 V		0.8	V
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 2.7 V		–12	mA
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 2.7 V		12	mA
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: Unused inputs must be held high or low to prevent them from floating.

PRODUCT PREVIEW

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}†	MIN	TYP‡	MAX	UNIT
V_{OH}	I_{OH} = –100 μA	MIN to MAX	V_{CC}–0.2			V
	I_{OH} = – 12 mA	2.7 V	2.2			
		3 V	2.4			
	I_{OH} = – 24 mA	3 V	2.2			
V_{OL}	I_{OL} = 100 μA	MIN to MAX			0.2	V
	I_{OL} = 12 mA	2.7 V			0.4	
	I_{OL} = 24 mA	3 V			0.55	
I_I	V_I = 5.5 V or GND	3.6 V			±5	μA
I_{OZ}	V_O = 5.5 V or GND	3.6 V			±10	μA
I_{CC}	V_I = V_{CC} or GND, I_O = 0	3.6 V			10	μA
ΔI_{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	2.7 V to 3.6 V			500	μA
C_i	V_I = V_{CC} or GND	3.3 V				pF
C_o	V_O = V_{CC} or GND	3.3 V				pF

† For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.
‡ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

PRODUCT PREVIEW

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